

TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (U-MOSIV)

TPCP8202

Portable Equipment Applications

Motor Drive Applications

DC-DC Converters

- Lead(Pb)-Free
- Low drain-source ON-resistance: $R_{DS(ON)} = 19 \text{ m}\Omega$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 20 \text{ S}$ (typ.)
- Low leakage current: $I_{DSS} = 10 \text{ }\mu\text{A}$ (max)($V_{DS} = 30 \text{ V}$)
- Enhancement model: $V_{th} = 0.7 \text{ to } 1.4 \text{ V}$

($V_{DS} = 10 \text{ V}$, $I_D = 200 \text{ }\mu\text{A}$)

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

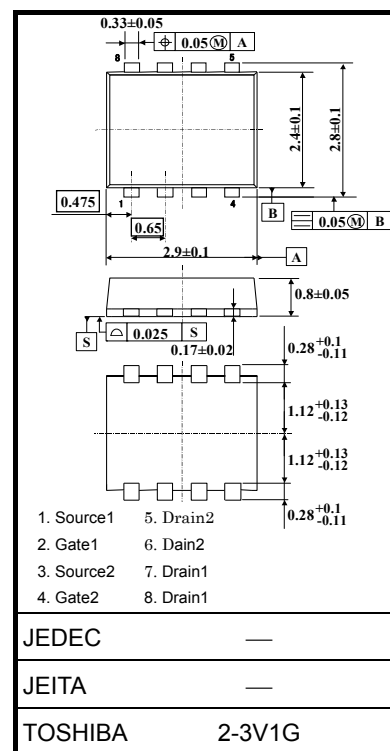
Characteristic		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	30	V
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)		V_{DGR}	30	V
Gate-source voltage		V_{GSS}	± 12	V
Drain current	DC (Note 1)	I_D	5.5	A
	Pulse (Note 1)	I_{DP}	22	
Drain power dissipation ($t = 5 \text{ s}$) (Note 2a)	Single-device operation (Note 3a)	P_D (1)	1.48	W
	Single-device value at dual operation (Note 3b)	P_D (2)	1.23	
Drain power dissipation ($t = 5 \text{ s}$) (Note 2b)	Single-device operation (Note 3a)	P_D (1)	0.58	
	Single-device value at dual operation (Note 3b)	P_D (2)	0.36	
Single-pulse avalanche energy (Note 4)		E_{AS}	7.86	mJ
Avalanche current		I_{AR}	5.5	A
Repetitive avalanche energy Single-device value at dual operation (Note 2a, 3b, 5)		E_{AR}	0.12	mJ
Channel temperature		T_{ch}	150	$^\circ\text{C}$
Storage temperature range		T_{stg}	-55 to 150	$^\circ\text{C}$

Note: For Notes 1 to 6, see the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

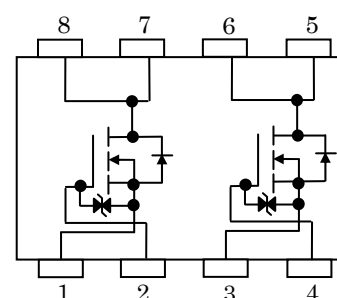
This transistor is an electrostatic-sensitive device. Handle with care.

Unit: mm

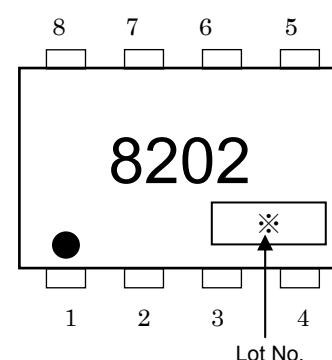


Weight: 0.017 g (typ.)

Circuit Configuration



Marking (Note 6)

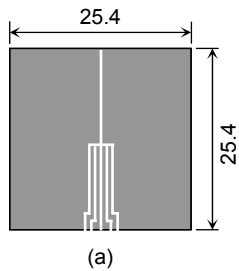


Thermal Characteristics

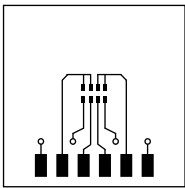
Characteristic		Symbol	Max	Unit
Thermal resistance, channel to ambient (t = 5 s) (Note 2a)	Single-device operation (Note 3a)	$R_{th (ch-a) (1)}$	84.5	°C/W
	Single-device value at dual operation (Note 3b)	$R_{th (ch-a) (2)}$	101.6	
Thermal resistance, channel to ambient (t = 5 s) (Note 2b)	Single-device operation (Note 3a)	$R_{th (ch-a) (1)}$	215.5	°C/W
	Single-device value at dual operation (Note 3b)	$R_{th (ch-a) (2)}$	347.2	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a) (b) Device mounted on a glass-epoxy board (b)



FR-4
25.4 × 25.4 × 0.8
(Unit: mm)



FR-4
25.4 × 25.4 × 0.8
(Unit: mm)

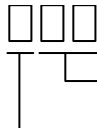
- Note 3: a) The power dissipation and thermal resistance values shown are for a single device. (During single-device operation, power is applied to one device only.)
b) The power dissipation and thermal resistance values shown are for a single device. (During dual operation, power is applied to both devices evenly.).

Note 4: $V_{DD} = 24\text{ V}$, $T_{ch} = 25^\circ\text{C}$ (initial), $L = 0.2\text{ mH}$, $R_G = 25\ \Omega$, $I_{AR} = 5.5\text{ A}$

Note 5: Repetitive rating: Pulse width limited by maximum channel temperature.

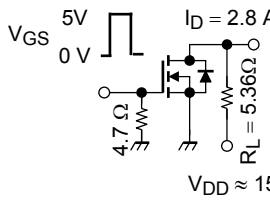
Note 6: ● on the lower left of the marking indicates Pin 1.

* Weekly code (three digits):



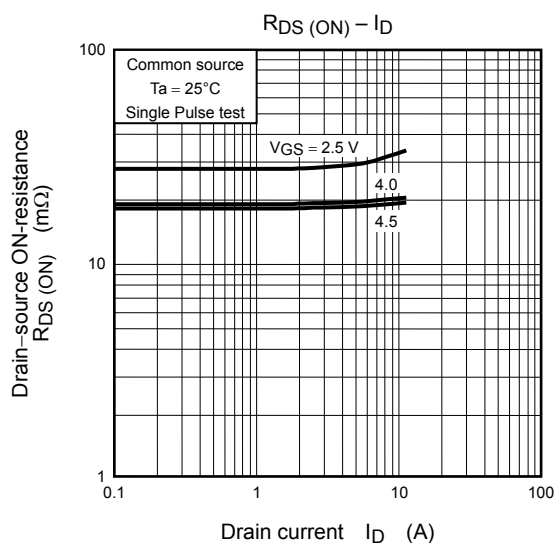
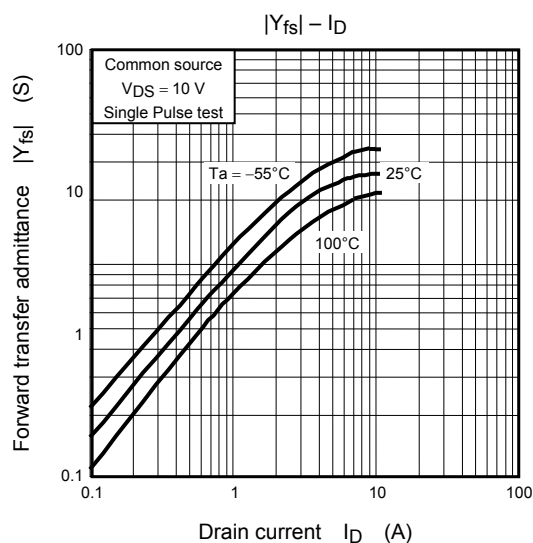
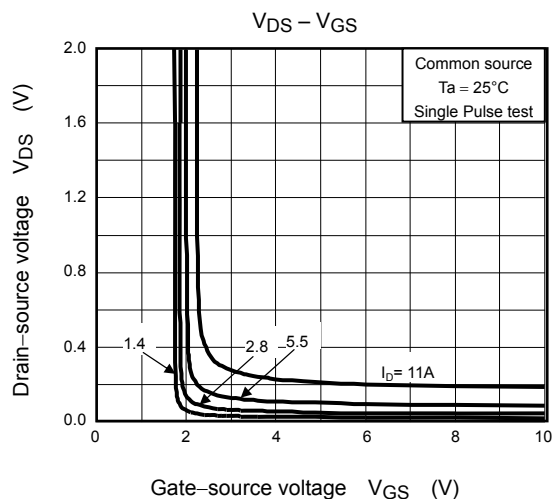
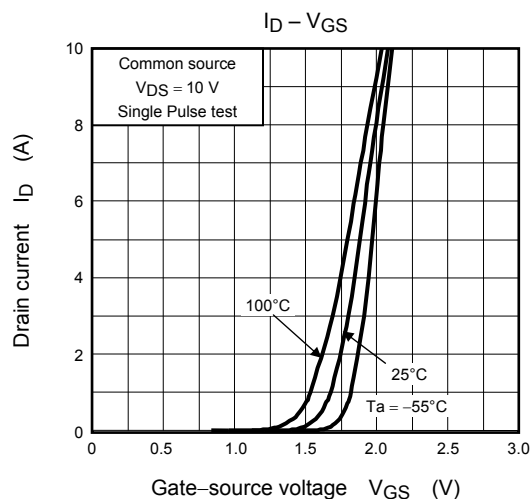
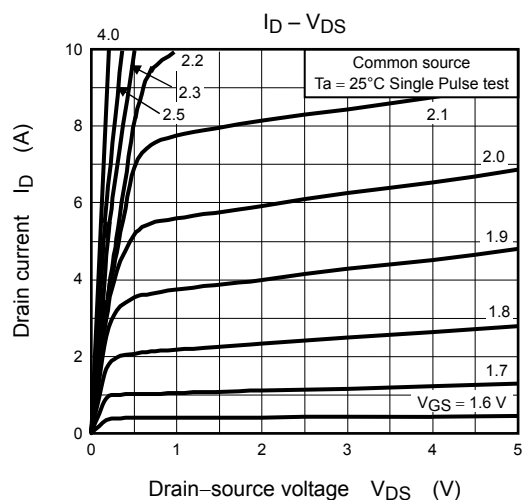
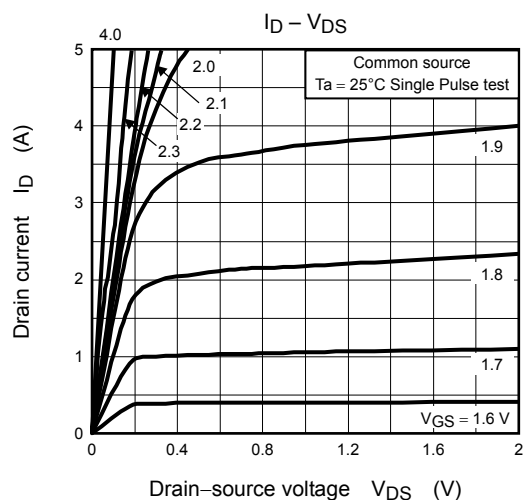
Week of manufacture
(01 for the first week of the year, continuing up to 52 or 53)
Year of manufacture
(The last digit of the year)

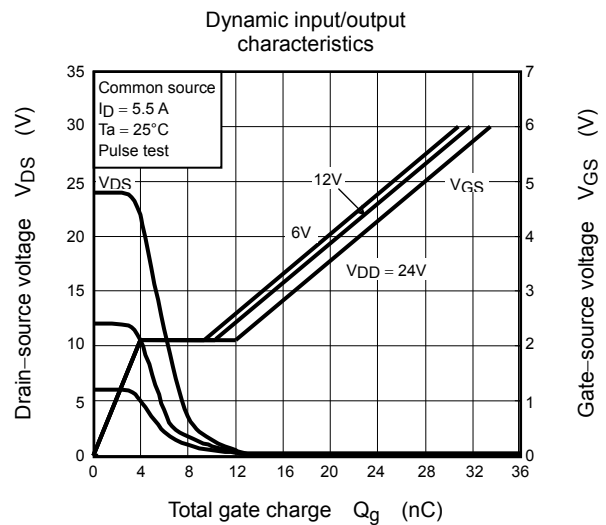
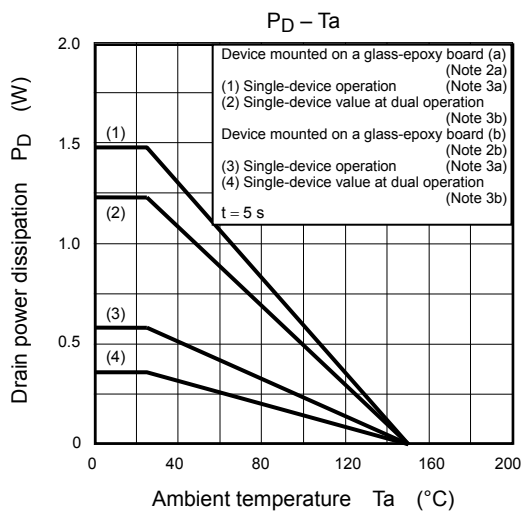
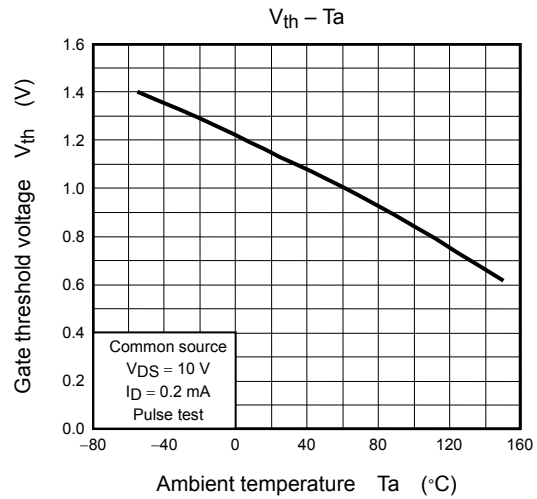
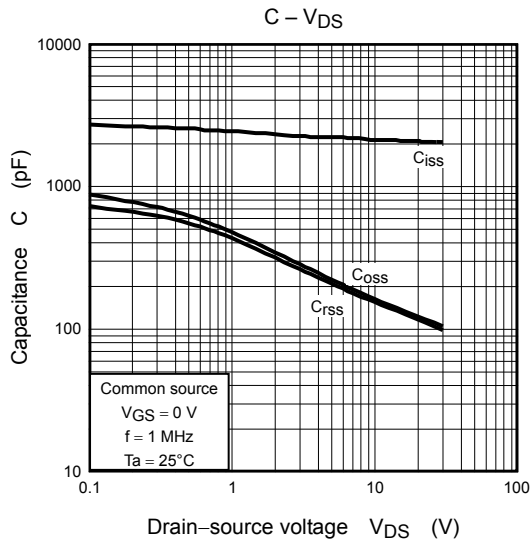
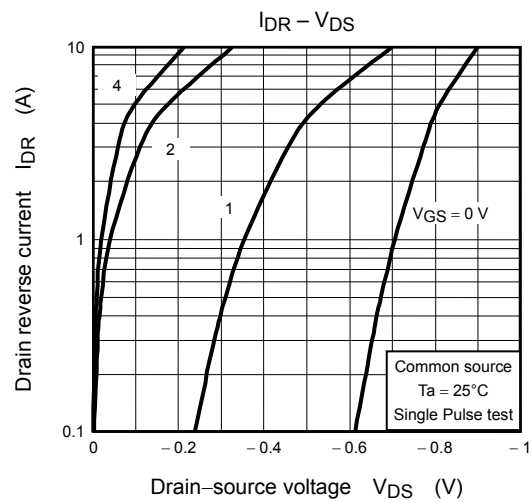
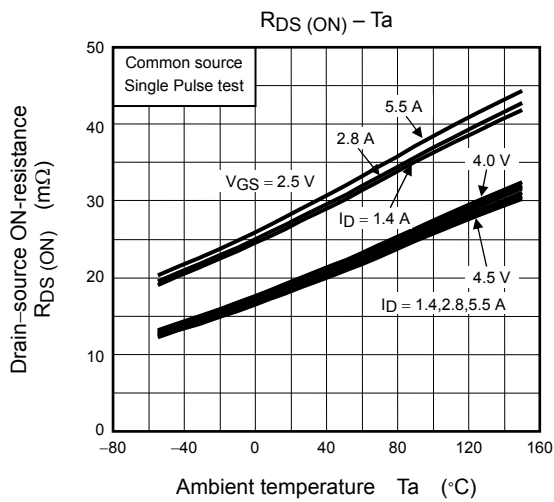
Electrical Characteristics (Ta = 25°C)

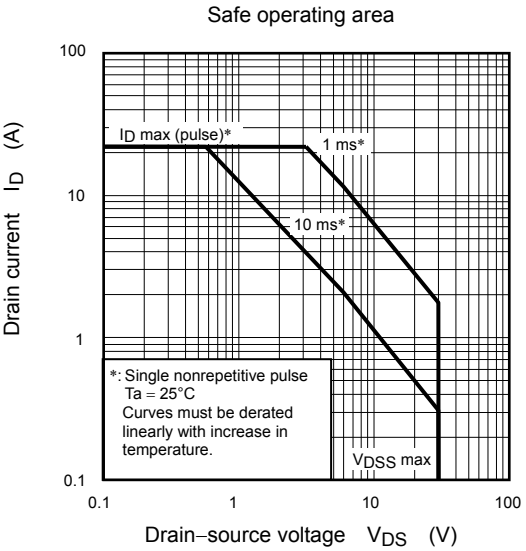
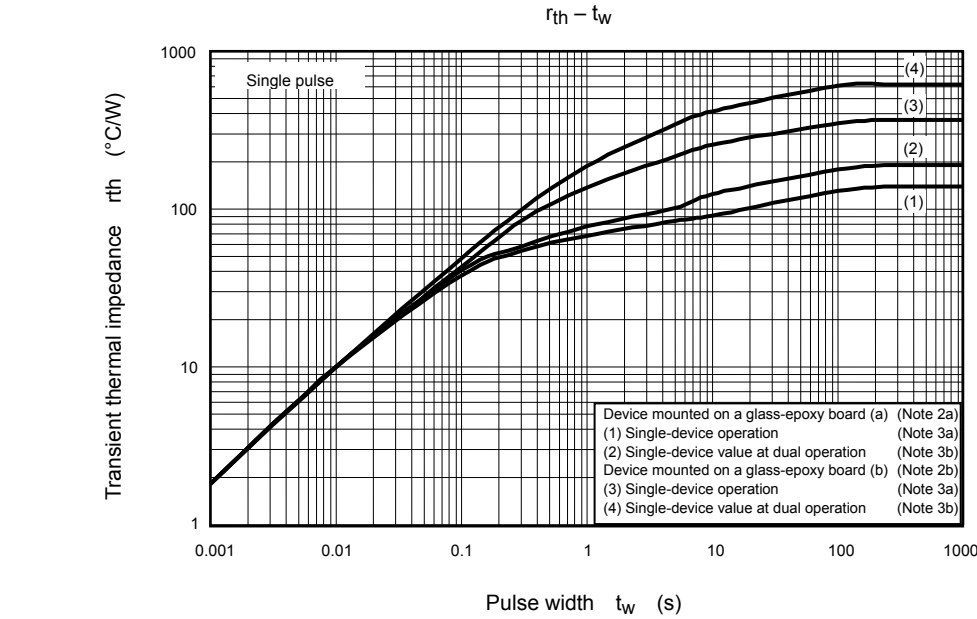
Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	$V_{GS} = \pm 10 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	± 10	μA
Drain cutoff current		I_{DSS}	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	10	μA
Drain-source breakdown voltage		$V_{(BR) DSS}$	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	30	—	—	V
		$V_{(BR) DSX}$	$I_D = 10 \text{ mA}, V_{GS} = -12 \text{ V}$	15	—	—	
Gate threshold voltage		V_{th}	$V_{DS} = 10 \text{ V}, I_D = 200 \mu\text{A}$	0.7	—	1.4	V
Drain-source ON-resistance		$R_{DS(ON)}$	$V_{GS} = 2.5 \text{ V}, I_D = 2.8 \text{ A}$	—	29	39	$\text{m}\Omega$
		$R_{DS(ON)}$	$V_{GS} = 4.0 \text{ V}, I_D = 2.8 \text{ A}$	—	20	24	
		$R_{DS(ON)}$	$V_{GS} = 4.5 \text{ V}, I_D = 2.8 \text{ A}$	—	19	23	
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10 \text{ V}, I_D = 2.8 \text{ A}$	10	20	—	S
Input capacitance		C_{iss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	—	2150	—	pF
Reverse transfer capacitance		C_{rss}		—	155	—	
Output capacitance		C_{oss}		—	165	—	
Switching time	Rise time	t_r	 $V_{GS} = 5 \text{ V}$ 0 V $I_D = 2.8 \text{ A}$ 4.7Ω 5.36Ω $R_L = 5.36 \Omega$ $V_{DD} \approx 15 \text{ V}$ Duty $\leq 1\%$, $t_w = 10 \mu\text{s}$	—	10	—	ns
	Turn-on time	t_{on}		—	20	—	
	Fall time	t_f		—	19	—	
	Turn-off time	t_{off}		—	90	—	
Total gate charge (gate-source plus gate-drain)		Q_g	$V_{DD} \approx 24 \text{ V}, V_{GS} = 5 \text{ V}, I_D = 5.5 \text{ A}$	—	28	—	nC
Gate-source charge1		Q_{gs1}		—	4	—	
Gate-drain ("Miller") charge		Q_{gd}		—	8	—	

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Drain reverse current	Pulse (Note 1)	I_{DRP}	—	—	—	22	A
Forward voltage (diode)		V_{DSF}	$I_{DR} = 5.5 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	-1.2	V







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20070701-EN GENERAL

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